

# 2STD1665

# Low voltage fast-switching NPN power transistor

### Features

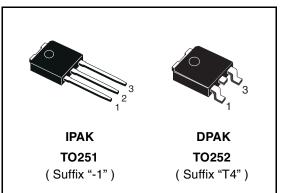
- Very low collector to emitter saturation volatage
- High current gain characteristic
- Fast-switching speed
- Through-hole IPAK (TO-251) power package in tube (suffix"-1")
- Surface mounting DPAK (TO-252) power package in tape & reel (suffix"T4")

## **Applications**

- Ccfl drivers
- Voltage regulators
- Relay drivers
- High efficiency low voltage switching applications

## Description

The device is manufactured in NPN Planar Technology by using a "Base Island" layout. The resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.



#### Figure 1. Internal schematic diagram

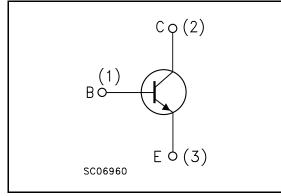


Table 1.	Device	summary
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Order code	Marking	Package	Packing
2STD1665T4	D1665	DPAK	Tape & reel
2STD1665-1	D1665	IPAK	Tube

	March	2008
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# 1 Electrical ratings

Table 2.	Absolute maximum rating	
	Absolute maximum rating	

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-base voltage ( $I_E = 0$ )	150	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	65	V
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	7	V
Ι <sub>C</sub>	Collector current	6	А
I <sub>CM</sub> Collector peak current (t <sub>P</sub> < 5ms)		20	А
۱ <sub>B</sub>	Base current	1	А
P <sub>tot</sub>	Total dissipation at $T_c = 25 \ ^{\circ}C$	15	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

### Table 3. Thermal data

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Symbol	Parameter	Value	Unit
R <sub>thj-amb</sub>	Thermal resistance junction-case max	8.33	°C/W



# 2 Electrical characteristics

(T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test c	onditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current $(I_E = 0)$	-	T <sub>C</sub> = 100 °C			50 1	nΑ μA
I <sub>EBO</sub>	Emitter cut-off current $(I_{\rm C} = 0)$	V <sub>EB</sub> = 7 V				10	nA
V <sub>(BR)CBO</sub> <sup>(1)</sup>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	l <sub>C</sub> = 100 μΑ		150			v
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	l <sub>C</sub> = 10 mA		65			v
V <sub>(BR)EBO</sub> <sup>(1)</sup>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 100 μA		7			v
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_{C} = 100 \text{ mA}$ $I_{C} = 1 \text{ A}$ $I_{C} = 2 \text{ A}$ $I_{C} = 6 \text{ A}$ $I_{C} = 6 \text{ A}$	$I_{B} = 5 mA$ $I_{B} = 50 mA$ $I_{B} = 50 mA$ $I_{B} = 150 mA$ $I_{B} = 300 mA$		50 100 260 230	50 120 200 600 380	mV mV mV mV mV
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	I <sub>C</sub> = 4 A	I <sub>B</sub> = 200 mA		1	1.15	V
V <sub>BE(on)</sub> <sup>(1)</sup>	Base-emitter On voltage	I <sub>C</sub> = 4 A	V <sub>CE</sub> = 1 V		0.85	1	V
h <sub>FE</sub>	DC current gain	$I_C = 10 \text{ mA}$ $I_C = 2 \text{ A}$ $I_C = 5 \text{ A}$ $I_C = 10 \text{ A}$	$V_{CE} = 1 V$ $V_{CE} = 1 V$ $V_{CE} = 1 V$ $V_{CE} = 1 V$	150 150 90 30	320 310 175 65	350	
C <sub>CBO</sub>	Collector-base capacitance	V <sub>CB</sub> = 10 V	f = 1 MHz		45		pF
t <sub>ON</sub> t <sub>s</sub> t <sub>f</sub>	Resistive load Turn-on time Storage time Fall time	I <sub>C</sub> = 3 A I <sub>B1</sub> = -I <sub>B2</sub> = 0.3	V <sub>CC</sub> = 10 V A		90 800 90		ns ns ns

Table 4. Electrical characteristics

1. Pulsed duration = 300  $\mu$ s, duty cycle  $\leq$ 1.5%.

### 2.1 Electrical characteristics (curves)

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Figure 2. Output characteristics
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Figure 3. DC current gain

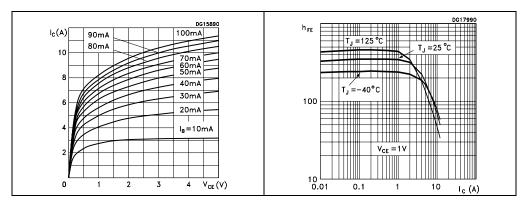
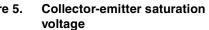


Figure 4. Collector-emitter saturation Figure 5. Construction Voltage



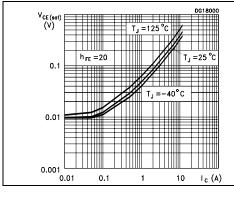


Figure 6. Base-emitter saturation voltage

 $h_{FE} = 20$ 

T<sub>J</sub> =25 °C

0.1

111

1

T<sub>J</sub> =125 °C

V<sub>BE (sat)</sub> (V)

1.1

1.0

0.9

0.8

0.7

0.6

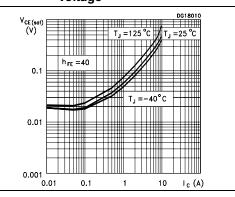
0.5

0.4

0.3

0.01

 $T_1 = -40^{\circ}$ 



Base-emitter on voltage

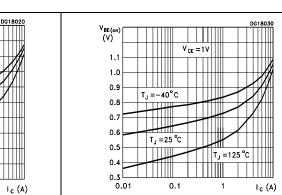


Figure 7.

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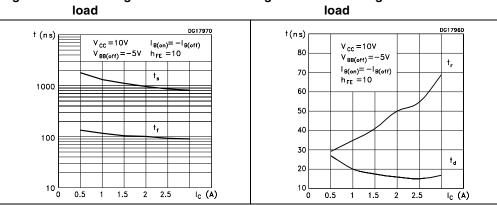
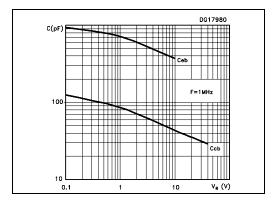


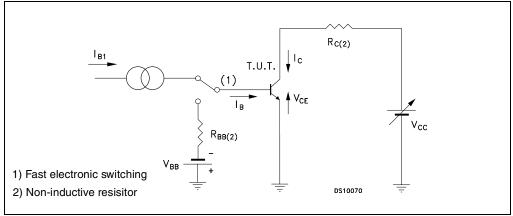
Figure 8. Switching times resistive Figure 9. Switching times resistive

Figure 10. Capacitance



#### 2.2 **Test circuit**



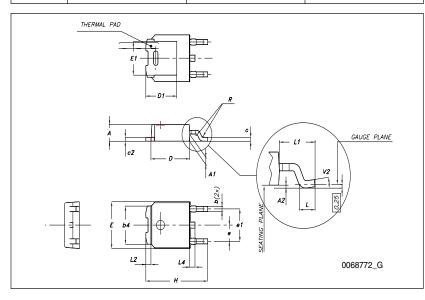


## 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

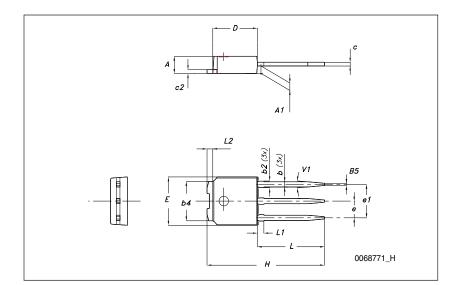


TO-252 (DPAK) mechanical data			
DIM.		mm.	
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
с	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
н	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °



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TO-251 (IPAK) mechanical data			
DIM.		mm.	
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.3	
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
е		2.28	
e1	4.40		4.60
н		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10 °	



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# 4 Revision history

### Table 5. Document revision history

Date	Revision	Changes
08-May-2006	1	Initial release
27-Mar-2008	2	New graphics



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